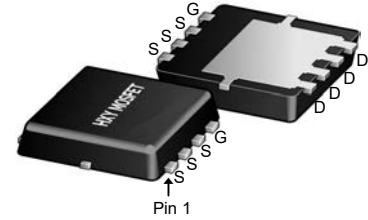




Description

The SIR462DP-T1-GE3 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6-8L

General Features

$V_{DS} = 30V$ $I_D = 50A$

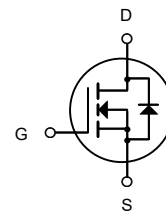
$R_{DS(ON)} < 8.5m\Omega$ $V_{GS} = 10V$

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SIR462DP-T1-GE3	DFN5X6-8L	HXY MOSFET	5000

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	60	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	38	A
I_{DM}	Pulsed Drain Current ²	200	A
EAS	Single Pulse Avalanche Energy ³	36	mJ
I_{AS}	Avalanche Current	50	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	31	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	27	$^\circ C/W$

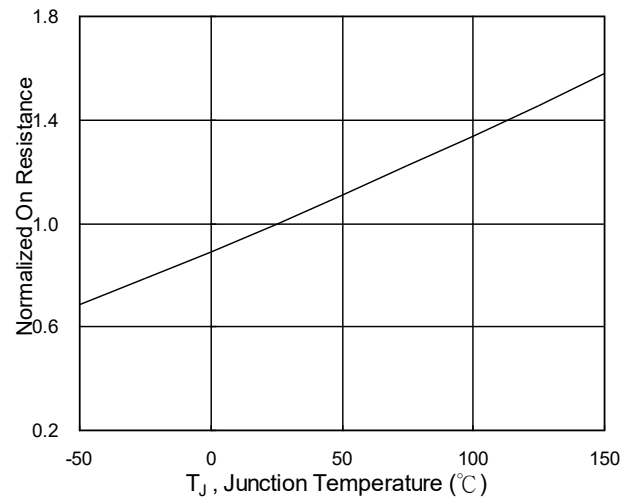
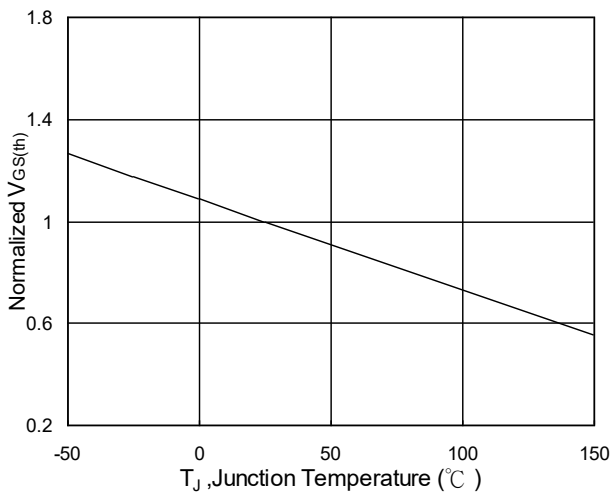
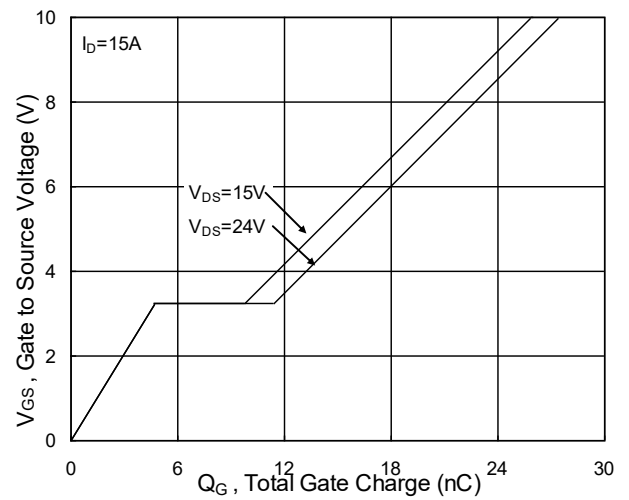
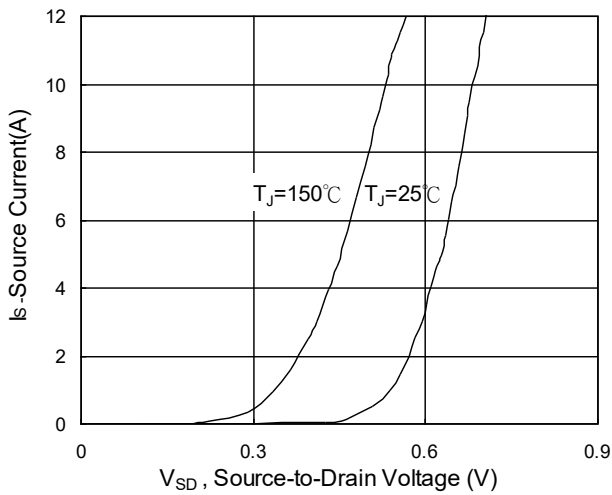
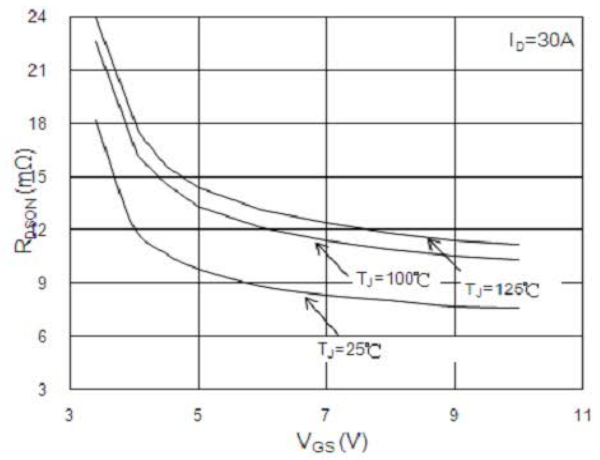
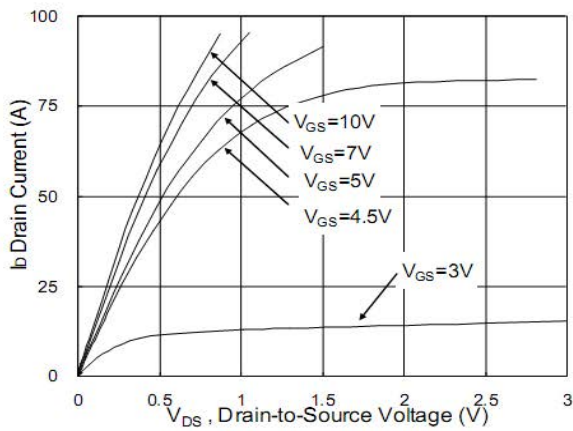


Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\ \mu A$	30	---	---	V	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=24V$	---	---	1	μA	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	± 100	nA	
$V_{GS(th)}$	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\ \mu A$	1.2	1.5	2.5	V	
$R_{DS(on)}$	Drain-Source On Resistance ²	$V_{GS}=10V, I_D=30A$	---	6.5	8.5	m Ω	
		$V_{GS}=4.5V, I_D=15A$	---	11	14		
G_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=30A$	---	38	---	S	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1MHz$	---	1317	1844	pF	
C_{oss}	Output Capacitance		---	163	228		
C_{rss}	Reverse Transfer Capacitance		---	131	183		
$t_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, I_D=15A, R_L=\Omega$	---	4.6	9.2	ns	
t_r	Rise Time		---	12.2	22	ns	
$t_{d(off)}$	Turn-Off Delay Time		$V_{GS}=15V, R_G=3.3\Omega$	---	26.6	53	ns
t_f	Fall Time		---	8	16	ns	
Q_g	Total Gate Charge		$V_{GS}=4.5V, V_{DS}=15V,$ $I_D=15A$	---	21	17.6	nC
Q_{gs}	Gate-Source Charge	---		2.35	5.9	nC	
Q_{gd}	Gate-Drain "Miller" Charge	---		5.9	7.1	nC	
V_{SD}	Source-Drain Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A$	---	---	1	V	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V, \text{ Force Current}$	---	---	58	A	
I_{SM}	Pulsed Source Current ^{2, 5}		---	---	115	A	
t_{rr}	Reverse Recovery Time	$I_F=30A,$ $di/dt=100A/\mu s, T_J=25\text{ }^\circ\text{C}$	---	9.2	---		
Q_{rr}	Reverse Recovery Charge		---	2	---		



Typical Characteristics



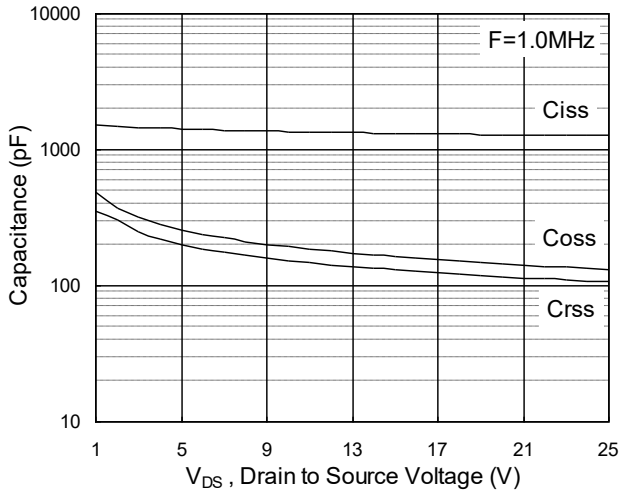


Fig.7 Capacitance

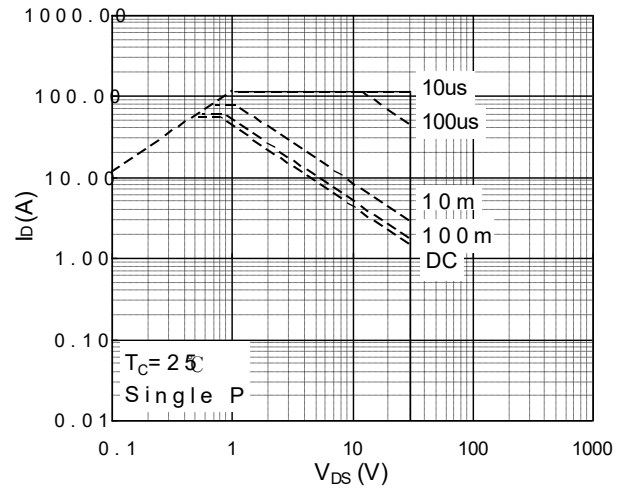


Fig.8 Safe Operating Area

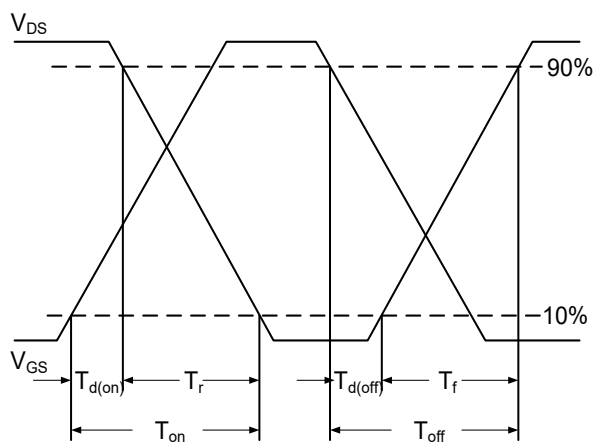
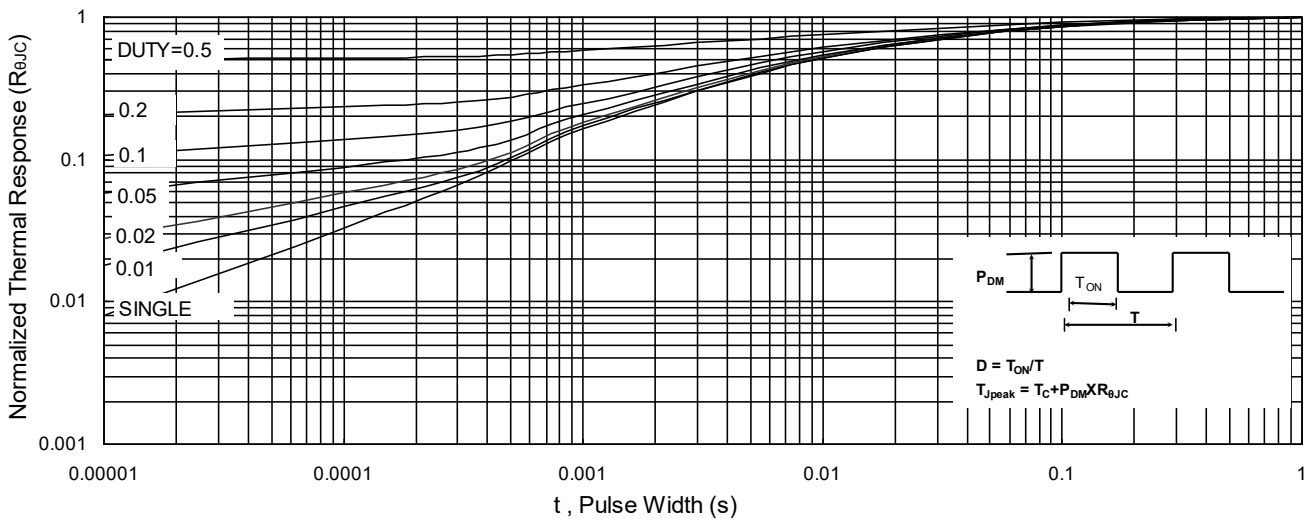
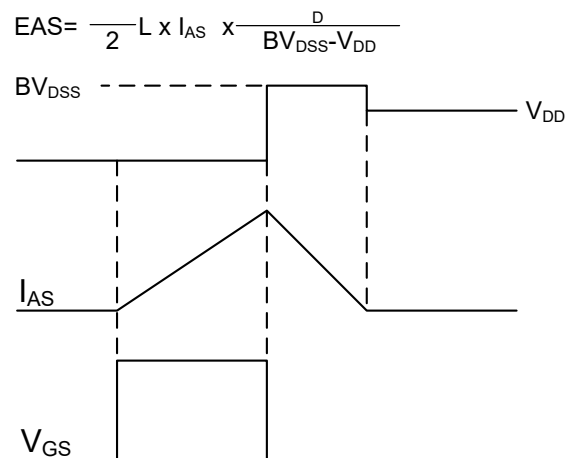
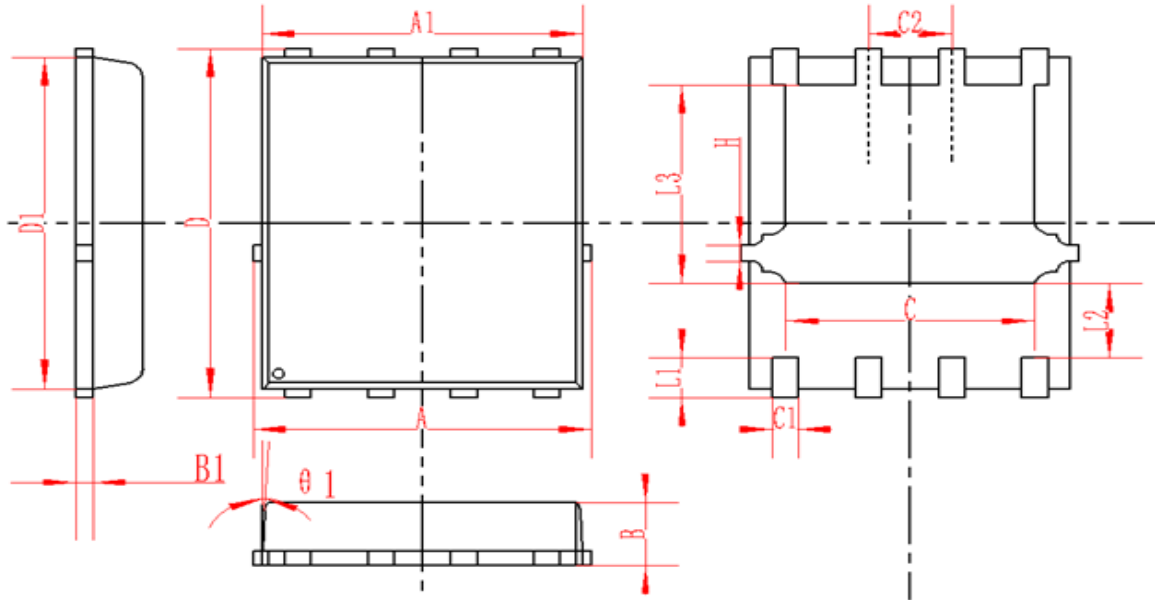


Fig.10 Switching Time Waveform





DFN5X6-8L Package Information



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.95	5	5.05	0.195	0.197	0.199
A1	4.82	4.9	4.98	0.190	0.193	0.196
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.67	5.75	5.83	0.223	0.226	0.230
B	0.9	0.95	1	0.035	0.037	0.039
B1	0.254REF			0.010REF		
C	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2	1.27TYP			0.5TYP		
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
H	0.24	0.25	0.26	0.009	0.010	0.010



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